

## Descriptions

- Switching application
- Interface circuit and driver circuit application

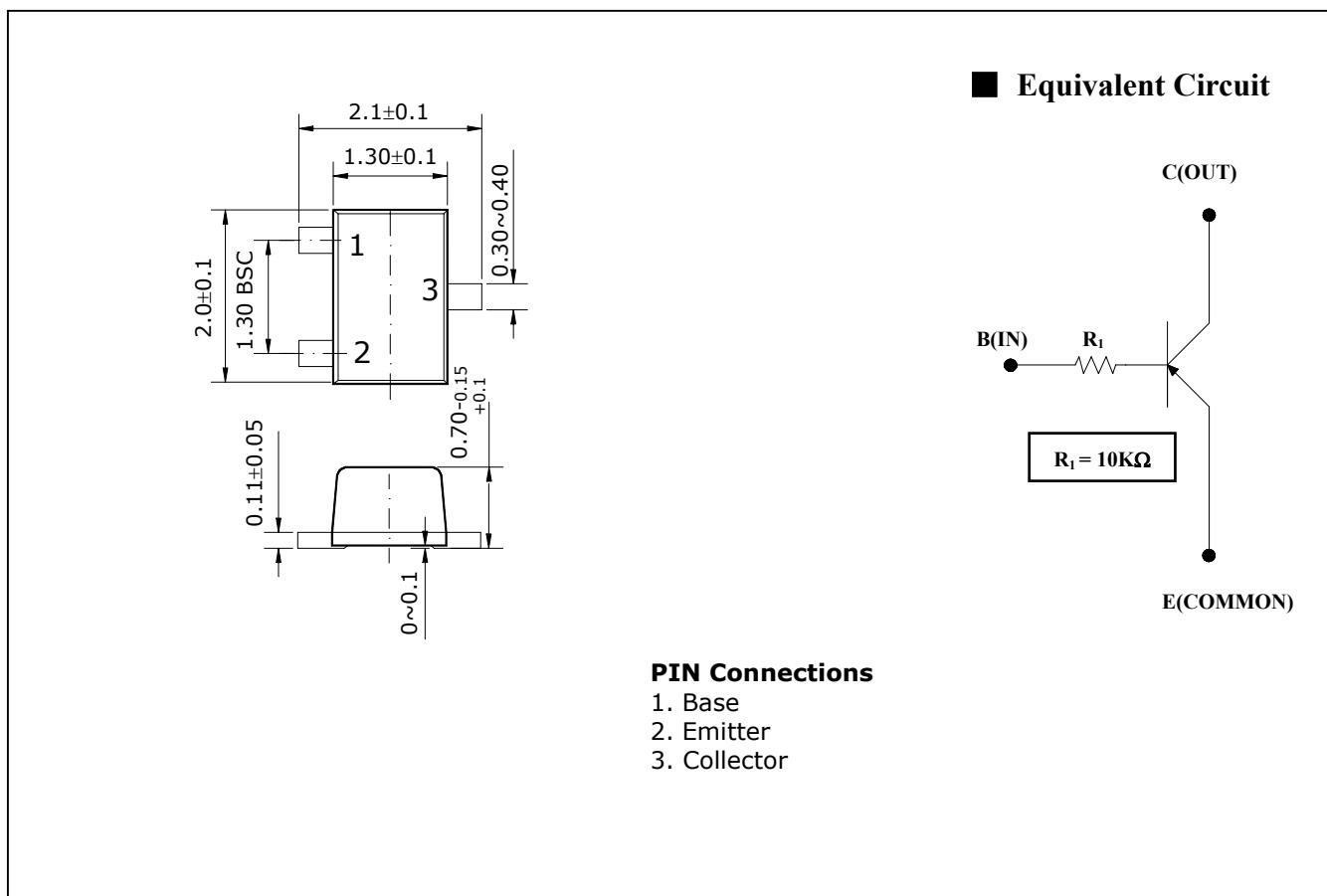
## Features

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- High packing density

## Ordering Information

Type NO.	Marking	Package Code
SRA2211UF	DR	SOT-323F

## Outline Dimensions

**unit : mm**


**Absolute maximum ratings**

(Ta=25°C)

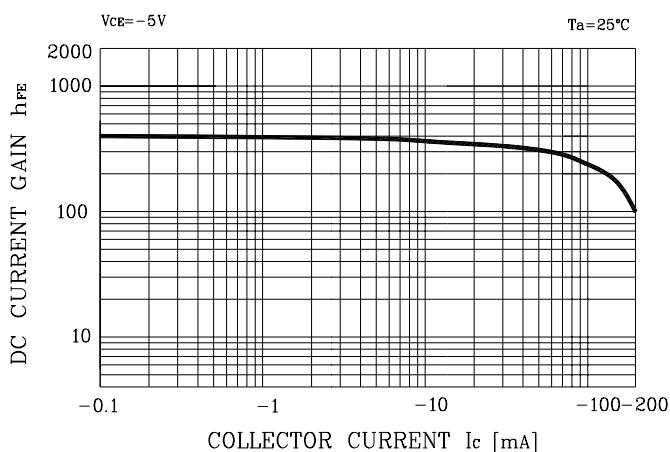
Characteristic	Symbol	Ratings	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-50	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current	I <sub>C</sub>	-100	mA
Power Dissipation	P <sub>D</sub>	200	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ 150	°C

**Electrical Characteristics**

(Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> =-50V, I <sub>E</sub> =0	-	-	-500	nA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0	-	-	-500	nA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1mA	120	-	-	-
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> =-0.5mA	-	-0.1	-0.3	V
Transition Frequency	f <sub>T</sub> <sup>*</sup>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-5mA	-	250	-	MHz
Input Resistance	R <sub>I</sub>	-	-	10	-	KΩ

\* : Characteristic of Transistor Only

**Electrical Characteristic Curves****Fig. 1 h<sub>FE</sub> - I<sub>C</sub>****Fig. 2 V<sub>CE(SAT)</sub> - I<sub>C</sub>**